Updated: May 2022 1(4)

# EIFys PD1s Photodetector Datasheet



## 1. Product Description and Key Features

ElFys PD series photodiode products consist of ElFys patented Black Silicon Induced Junction Technology. Product patent information can be found at <a href="https://www.elfys.fi/index.php/technology/patent/">https://www.elfys.fi/index.php/technology/patent/</a>. ElFys PD series photodiode products provide superior performance in photosensitivity across a wide spectrum of wavelengths, from deep UV, Vis to NIR. ElFys PD series photodiode products are suitable for various high precision photometry applications.

### Key features:

- Enhanced photosensitivity to UV, Vis and NIR
- H model provides low capacitance
- M model provides low dark current

Name	Photosensi- tive area (mm)	Chip Outline Dimension (mm)	Reverse Voltage (V) Max.	Guard ring connection	Packaging Options	Window / Fil- ter Options
PD1sH	10 × 10	1 5 7 1 5	10	No	Chip /	No window /
PD1sM	1.0 x 1.0	1.5 x 1.5	10	No	PCB / TO-46	Schott UV- glass

Note: The environmental protection of the photodetector depends on the selected packaging option. ElFys provides customized packaging solutions based on customer specifications.



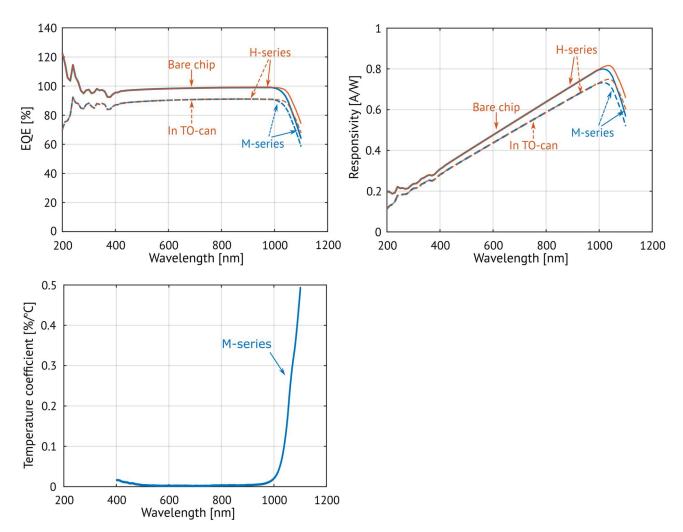
Updated: May 2022 2(4)

# 2. Electrical and Optical Performance

Part number	Spectral response	Peak response wave-	Photosensitivity			У	Dark current @	Capacitance @	Shunt re- sistance	Noise equivalent
, maniber	range		λ <sub>p</sub> Typ.	200 nm	630 nm	930 nm	V <sub>R</sub> =10mV, Max.	V <sub>R</sub> =0V, f=100kHz.	@	power NEP
		length, λ <sub>p</sub>		Тур.	Тур.	Тур.	мах.	Typ.	V <sub>R</sub> =10mV, Min.	@ λ <sub>p</sub> , Max.
	nm	nm	A/W	A/W	A/W	A/W	pA	pF	МΩ	W/√Hz
PD1sH	170-1100	1040	0.81	0.20	0.50	0.74	255	11	39	2.7×10 <sup>-14</sup>
PD1sM		1010	0.80			0.73	12	20	830	5.8×10 <sup>-15</sup>

Note: All data are specified at typical ambient temperature (25°C) and under normal working conditions. Photosensitivity performance will be affected by the optical properties of the window and filter applied in the packaging or end application. Photodiode characteristics, including photosensitivity may degrade when exposed to UV below 240nm. Potential degradation depends on total exposure dose and ambient conditions.

# 3. Spectral Response (Typical)

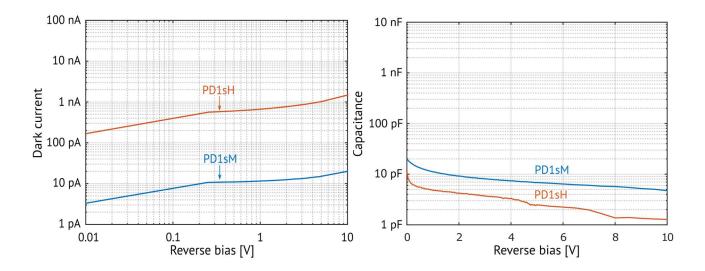


Note: the temperature coefficient in the range 200-400 nm can be provided upon customer request.

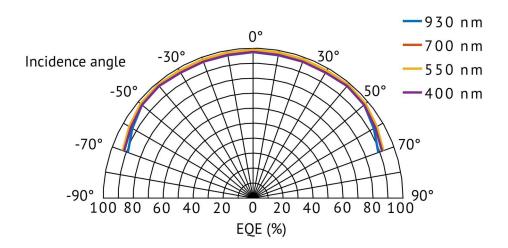


Updated: May 2022 3(4)

# 4. Dark Current and Capacitance vs Reverse Bias (Typical)



# 5. Angular responsivity



Note: Angle-dependent photosensitivity is measured from a process control monitor photodiode without window or filter.



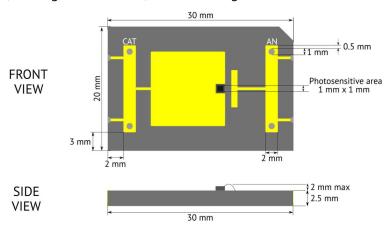
Updated: May 2022 4(4)

## 6. Packaging options

### **PCB**

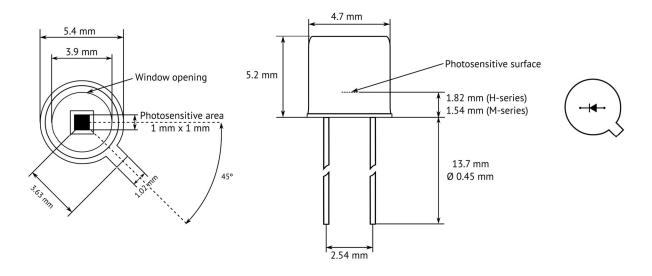
The photodetector is available by default on a demonstration board (30mm x 20mm). Customized demonstration board is available upon request according to customer specifications.

The electrical connections are anode (AN) and cathode (CAT). The default demonstration board is suitable for Surface Mount, Through Hole Mount, and Soldering Wire.



## **TO-46**

Another packaging option is TO-46 with Schott UV-glass. Other window materials and/or anti-reflective coatings of window are also available upon request. The cathode contact is connected to the body of the can.



ElFys, Inc. reserves the right to change product specification without prior notice.

